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Continuity of ordering part numbers
Infineon continues to support existing part numbers. Please continue to use the ordering part numbers listed in the datasheet for ordering.

CY62146ESL MoBL

4-Mbit (256K × 16) Static RAM

Features

- Very high speed: 45 ns
- Wide voltage range: 2.2 V to 3.6 V and 4.5 V to 5.5 V
- Ultra low standby power
  - Typical Standby current: 2.5 µA
  - Maximum Standby current: 7 µA
- Ultra low active power
  - Typical active current: 3.5 mA at f = 1 MHz
- Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features
- Automatic power down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 44-pin thin small outline package (TSOP) II package

Functional Description

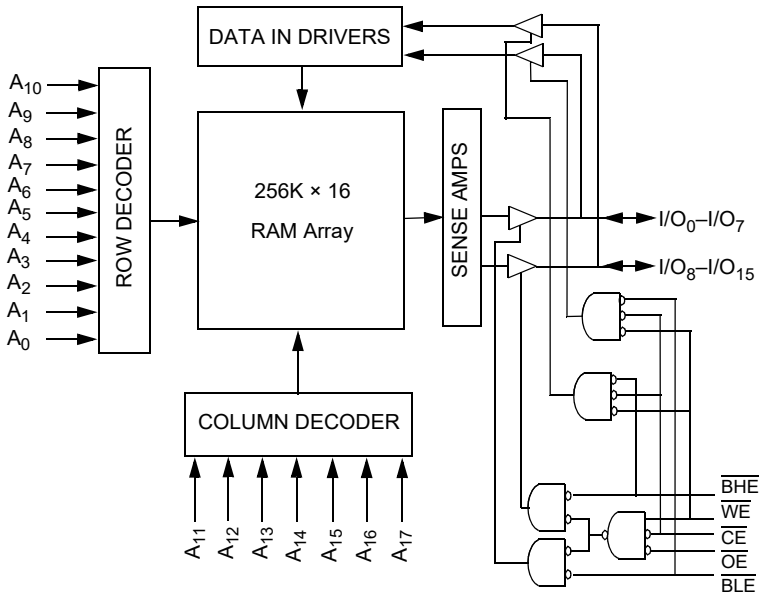
The CY62146ESL is a high performance CMOS static RAM organized as 256K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ($\overline{CE}$ HIGH). The input and output pins (I/O_0 through I/O_{15}) are placed in a high impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH) or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

To write to the device, take Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7) is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

To read from the device, take Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins appears on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory appears on I/O_8 to I/O_{15}. See the Truth Table on page 11 for a complete description of read and write modes.

For a complete list of related documentation, click here.

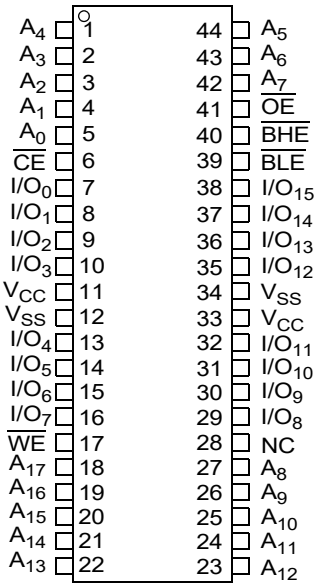
Logic Block Diagram



Contents

Pin Configurations

Figure 1. 44-pin TSOP II pinout (Top View) [1]



Product Portfolio

Product	Range	V_{CC} Range (V) [2]	Speed (ns)	Power Dissipation					
				Operating I_{CC}, (mA)				Standby, I_{SB2} (µA)	
				f = 1MHz		f = f_{max}			
				Typ [3]	Max	Typ [3]	Max	Typ [3]	Max
CY62146ESL	Industrial	2.2 V–3.6 V and 4.5 V–5.5 V	45	3.5	6	15	20	2.5	7

Notes
1. NC pins are not connected on the die.
2. Datasheet specifications are not guaranteed for V_{CC} in the range of 3.6 V to 4.5 V.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V, and V_{CC} = 5 V, T_A = 25 °C.

Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature ..... –65 °C to +150 °C

Ambient temperature with power applied ..... –55 °C to +125 °C

Supply voltage to ground potential .....–0.5 V to 6.0 V

DC voltage applied to outputs in High Z State [4, 5] .....–0.5 V to 6.0 V

DC input voltage [4, 5] .....–0.5 V to 6.0 V

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) .....>2001 V

Latch up current .....>200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}[6]
CY62146ESL	Industrial	–40 °C to +85 °C	2.2 V–3.6 V, and 4.5 V–5.5 V

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		45 ns			Unit
				Min	Typ [7]	Max	
V_{OH}	Output high voltage	$2.2 \le V_{CC} \le 2.7$	I_{OH} = –0.1 mA	2.0	–	–	V
		$2.7 \le V_{CC} \le 3.6$	I_{OH} = –1.0 mA	2.4	–	–	
		$4.5 \le V_{CC} \le 5.5$	I_{OH} = –1.0 mA	2.4	–	–	
V_{OL}	Output low voltage	$2.2 \le V_{CC} \le 2.7$	I_{OL} = 0.1 mA	–	–	0.4	V
		$2.7 \le V_{CC} \le 3.6$	I_{OL} = 2.1mA	–	–	0.4	
		$4.5 \le V_{CC} \le 5.5$	I_{OL} = 2.1mA	–	–	0.4	
V_{IH}	Input high voltage	$2.2 \le V_{CC} \le 2.7$		1.8	–	V_{CC} + 0.3	V
		$2.7 \le V_{CC} \le 3.6$		2.2	–	V_{CC} + 0.3	
		$4.5 \le V_{CC} \le 5.5$		2.2	–	V_{CC} + 0.5	
V_{IL}	Input low voltage	$2.2 \le V_{CC} \le 2.7$		–0.3	–	0.6	V
		$2.7 \le V_{CC} \le 3.6$		–0.3	–	0.8	
		$4.5 \le V_{CC} \le 5.5$		–0.5	–	0.8	
I_{IX}	Input Leakage Current	$GND \le V_I \le V_{CC}$		–1	–	+1	µA
I_{OZ}	Output Leakage Current	$GND \le V_O \le V_{CC}$, Output Disabled		–1	–	+1	µA
I_{CC}	V_{CC} Operating Supply Current	$f = f_{max} = 1/t_{RC}$	$V_{CC} = V_{CCmax}$, I_{OUT} = 0 mA, CMOS levels	–	15	20	mA
		f = 1 MHz		–	3.5	6	
I_{SB1}[8]	Automatic CE Power down Current – CMOS Inputs	$\overline{CE} \ge V_{CC}$ – 0.2 V, $V_{IN} \ge V_{CC}$ – 0.2 V or $V_{IN} \le$ 0.2 V, f = f_{max} (Address and Data Only), f = 0 ($\overline{OE}$, $\overline{BHE}$, $\overline{BLE}$ and $\overline{WE}$), $V_{CC} = V_{CC(max)}$		–	2.5	7	µA
I_{SB2}[8]	Automatic CE Power down Current – CMOS Inputs	$\overline{CE} \ge V_{CC}$ – 0.2 V, $V_{IN} \ge V_{CC}$ – 0.2 V or $V_{IN} \le$ 0.2 V, f = 0, $V_{CC} = V_{CC(max)}$		–	2.5	7	µA

Notes

4. V_{IL}(min) = –2.0V for pulse durations less than 20 ns.
5. V_{IH}(max) = V_{CC} + 0.75 V for pulse durations less than 20 ns.
6. Full Device AC operation assumes a 100 µs ramp time from 0 to V_{CC} (min) and 200 µs wait time after V_{CC} stabilization.
7. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V, and V_{CC} = 5 V, T_A = 25 °C.
8. Chip enable ($\overline{CE}$) must be HIGH at CMOS level to meet the $I_{SB1}/I_{SB2}/I_{CCDR}$ spec. Other inputs can be left floating.

Capacitance

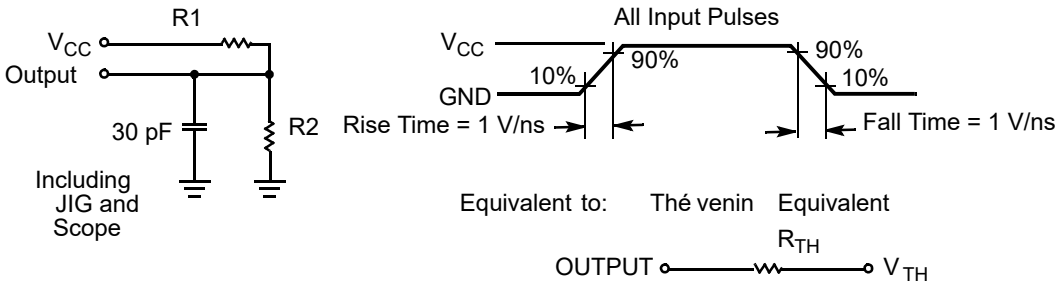
Parameter [9]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output capacitance		10	pF

Thermal Resistance

Parameter [9]	Description	Test Conditions	TSOP II	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Still Air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	57.92	°C/W
Θ_{JC}	Thermal resistance (junction to case)		17.44	°C/W

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms



Parameter	2.5 V	3.0 V	5.0 V	Unit
R1	16667	1103	1800	Ω
R2	15385	1554	990	Ω
R_{TH}	8000	645	639	Ω
V_{TH}	1.20	1.75	1.77	V

Note
9. Tested initially and after any design or process changes that may affect these parameters.

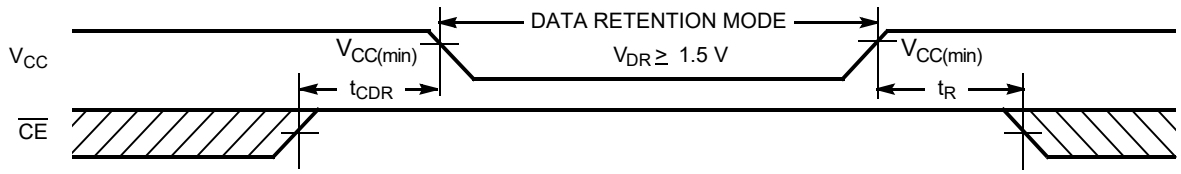
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions		Min	Typ [10]	Max	Unit
V_{DR}	V_{CC} for data retention			1.5	–	–	V
I_{CCDR} [11]	Data retention current	$\overline{CE} \geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V	V_{CC} = 1.5 V	–	3	8.8	µA
t_{CDR} [12]	Chip deselect to data retention time			0	–	–	ns
t_R [13]	Operation recovery time			45	–	–	ns

Data Retention Waveform

Figure 3. Data Retention Waveform



Notes

10. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 3 V, and V_{CC} = 5 V, T_A = 25 °C.
11. Chip enable ($\overline{CE}$) must be HIGH at CMOS level to meet the I_{SB1} / I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.
12. Tested initially and after any design or process changes that may affect these parameters.
13. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100$ µs or stable at $V_{CC(min)} \geq 100$ µs.

Switching Characteristics

Over the Operating Range

Parameter [14, 15]	Description	45 ns		Unit
		Min	Max	
Read Cycle				
t_{RC}	Read cycle time	45	–	ns
t_{AA}	Address to data valid	–	45	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}$ LOW to data valid	–	45	ns
t_{DOE}	$\overline{OE}$ LOW to data valid	–	22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z [16]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z [16, 17]	–	18	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z [16]	10	–	ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z [16, 17]	–	18	ns
t_{PU}	$\overline{CE}$ LOW to power up	0	–	ns
t_{PD}	$\overline{CE}$ HIGH to power down	–	45	ns
t_{DBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to data valid	–	22	ns
t_{LZBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Low Z [16]	5	–	ns
t_{HZBE}	$\overline{BLE}$/$\overline{BHE}$ HIGH to High Z [16, 17]	–	18	ns
Write Cycle [18, 19]				
t_{WC}	Write cycle time	45	–	ns
t_{SCE}	$\overline{CE}$ LOW to write end	35	–	ns
t_{AW}	Address setup to write end	35	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address setup to Write Start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	35	–	ns
t_{BW}	$\overline{BLE}$/$\overline{BHE}$ LOW to write end	35	–	ns
t_{SD}	Data Setup to write end	25	–	ns
t_{HD}	Data Hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High Z [16, 17]	–	18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z [16]	10	–	ns

Notes

14. In an earlier revision of this device, under a specific application condition, READ and WRITE operations were limited to switching of the byte enable and/or chip enable signals as described in the Application Note AN66311. However, the issue has been fixed and in production now, and hence, this Application Note is no longer applicable. It is available for download on our website as it contains information on the date code of the parts, beyond which the fix has been in production.
15. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3 V, and output loading of the specified I_{OL}/I_{OH} as shown in the Figure 2 on page 5.
16. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
17. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
18. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ or both = V_{IL}. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.
19. The minimum write cycle time for Write Cycle No. 4 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Waveforms

Figure 4. Read Cycle No. 1 (Address Transition Controlled) [20, 21]

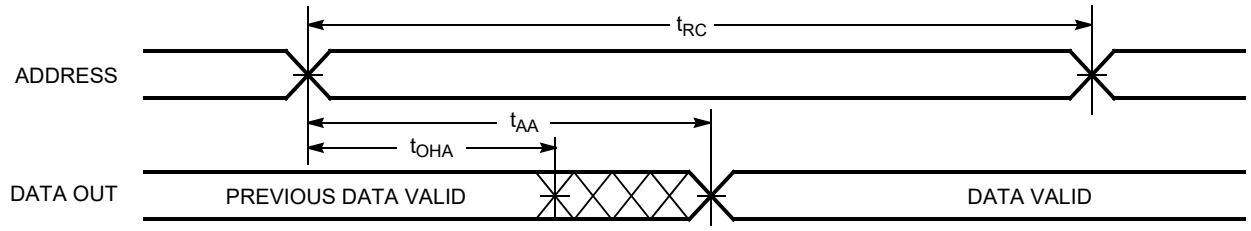
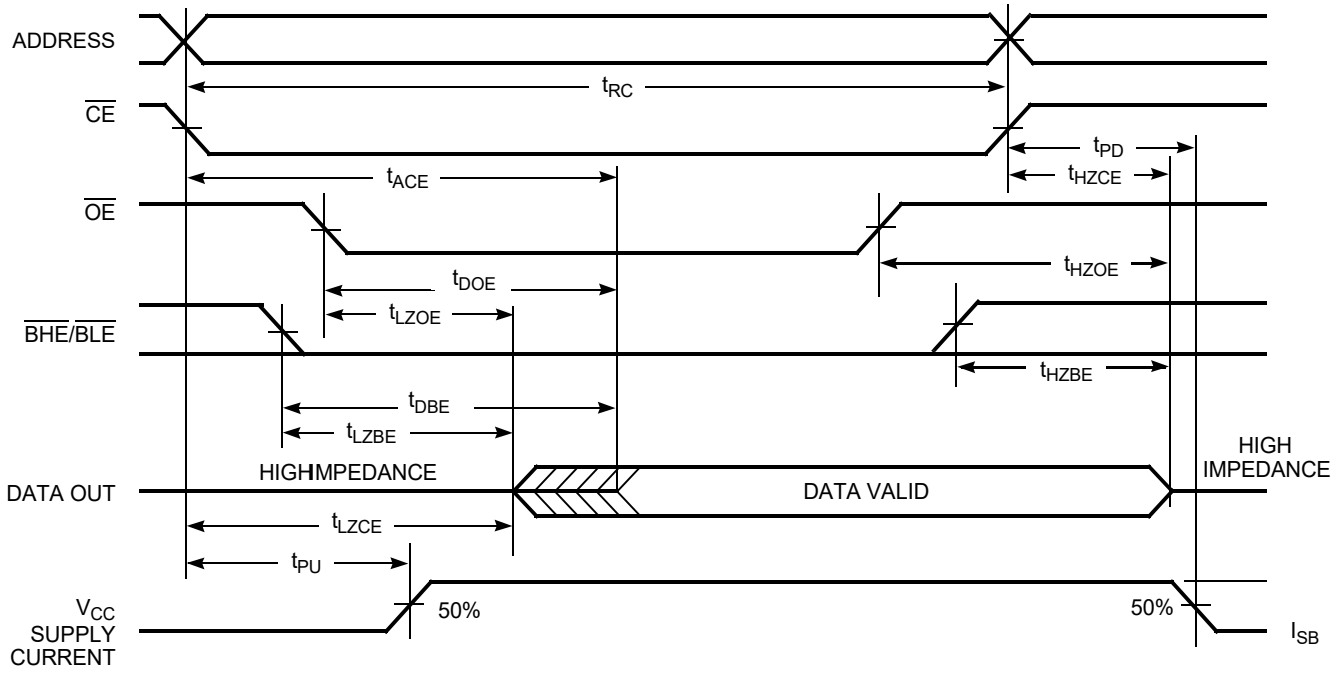


Figure 5. Read Cycle No. 2 ($\overline{OE}$ Controlled) [21, 22]



Notes
20. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}.
21. $\overline{WE}$ is HIGH for read cycle.
22. Address valid before or similar to $\overline{CE}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 ($\overline{WE}$ Controlled) [23, 24]

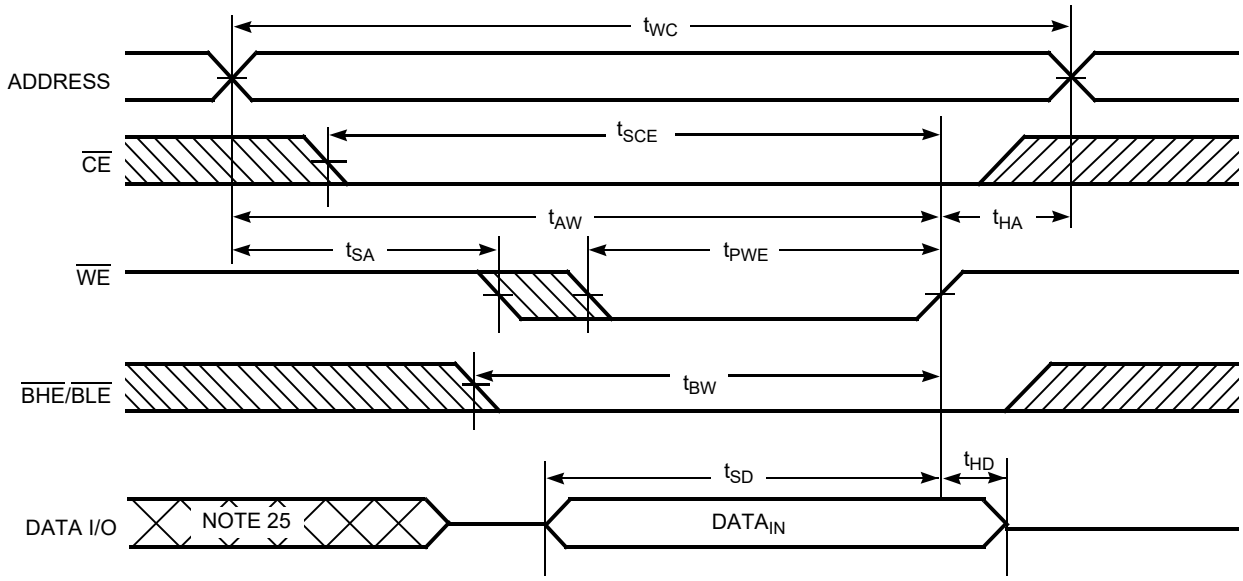
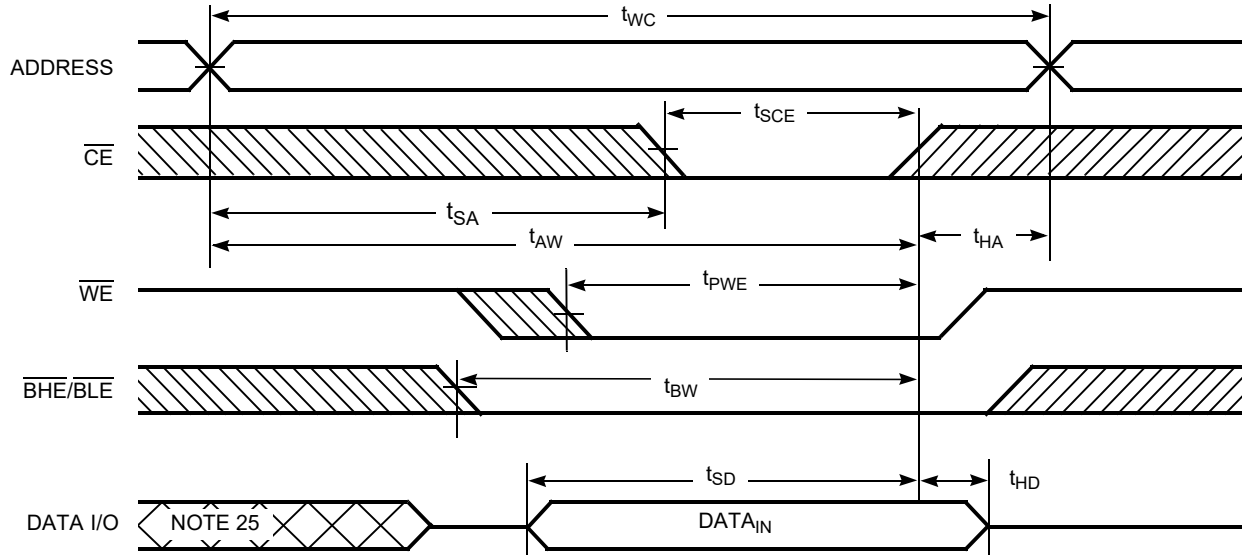


Figure 7. Write Cycle No. 2 ($\overline{CE}$ Controlled) [23, 24]



Notes

23. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ or both = V_{IL}. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.
24. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.
25. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 3 (BHE/BLE Controlled) [26]

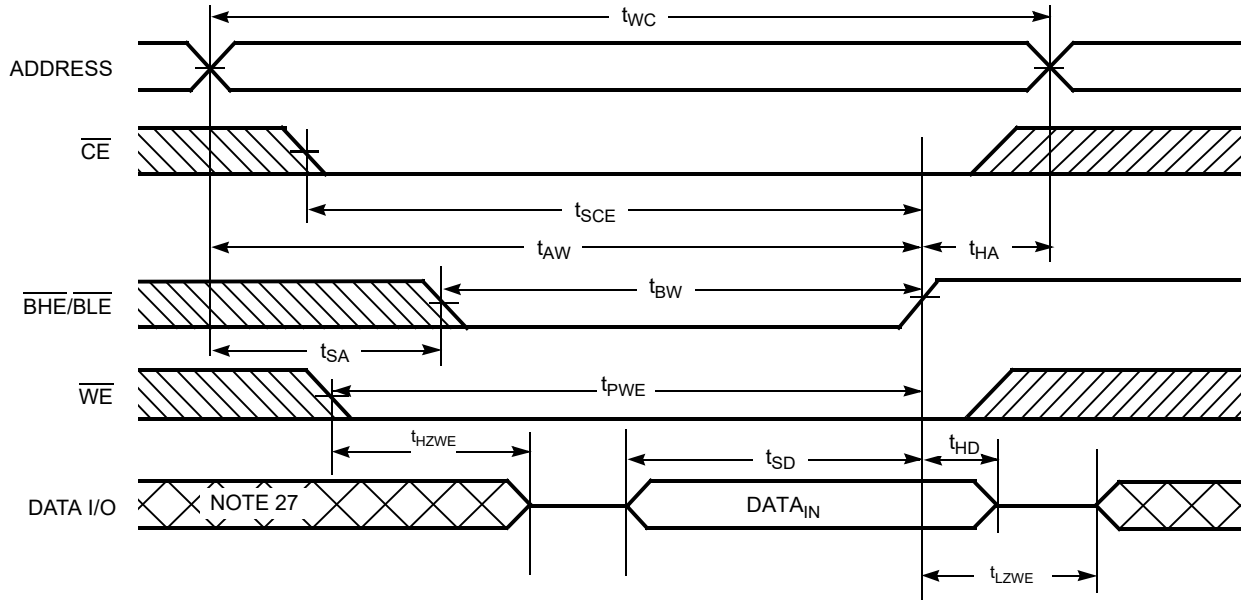
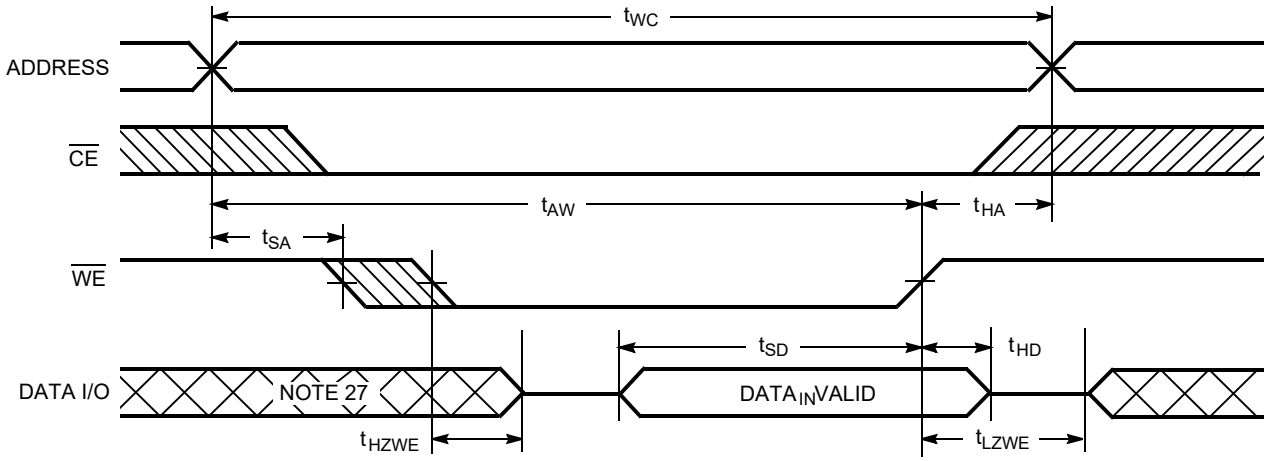


Figure 9. Write Cycle No. 4 (WE Controlled, OE LOW) [28]



Notes
26. If CE goes HIGH simultaneously with WE = V_{IH}, the output remains in a high impedance state.
27. During this period, the I/Os are in output state. Do not apply input signals.
28. The minimum write cycle time for Write Cycle No. 4 (WE Controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.

Truth Table

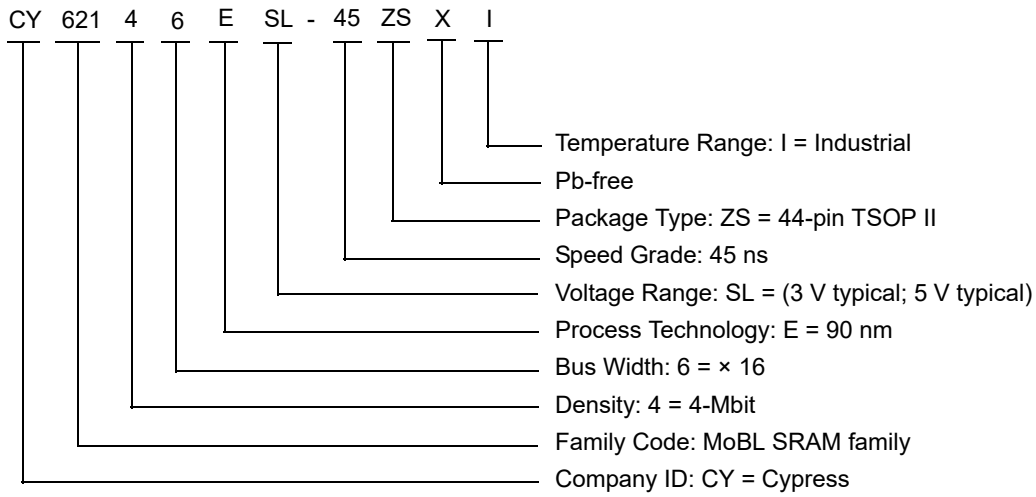
$\overline{CE}$ [29]	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High-Z	Deselect/Power down	Standby (I_{SB})
L	X	X	H	H	High-Z	Output disabled	Active (I_{CC})
L	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_0–I/O_7); I/O_8–I/O_{15} in High-Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High-Z	Read	Active (I_{CC})
L	H	H	L	L	High-Z	Output disabled	Active (I_{CC})
L	H	H	H	L	High-Z	Output disabled	Active (I_{CC})
L	H	H	L	H	High-Z	Output disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_0–I/O_7); I/O_8–I/O_{15} in High-Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0–I/O_7 in High-Z	Write	Active (I_{CC})

Note
29. Chip enable must be at CMOS levels (not floating). Intermediate voltage levels on this pin is not permitted.

Ordering Information

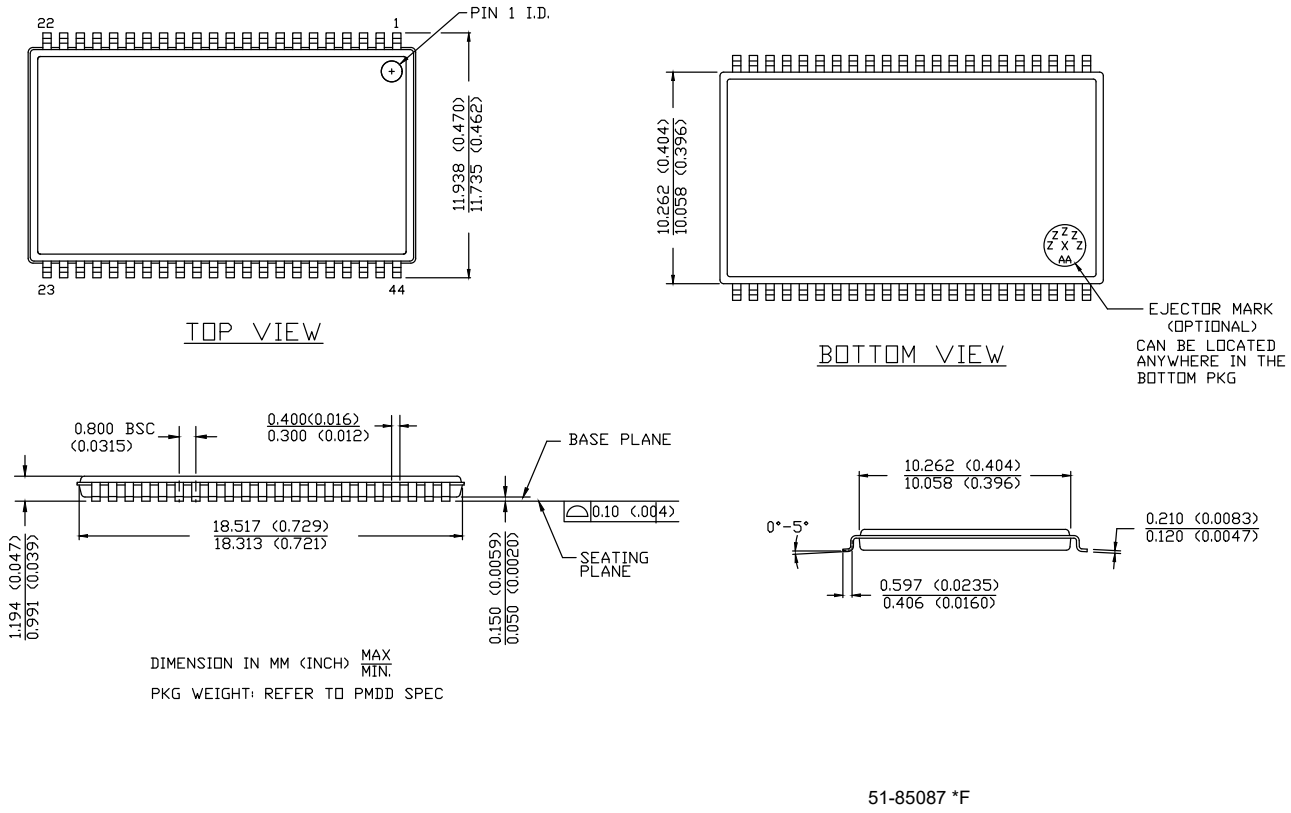
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62146ESL-45ZSXI	51-85087	44-pin TSOP Type II (Pb-free)	Industrial

Ordering Code Definitions



Package Diagram

Figure 10. 44-pin TSOP II (18.4 × 10.2 × 1.194 mm) Package Outline, 51-85087



Acronyms

Acronym	Description
$\overline{BHE}$	Byte High Enable
$\overline{BLE}$	Byte Low Enable
$\overline{CE}$	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
$\overline{OE}$	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
VFBGA	Very Fine-Pitch Ball Grid Array
$\overline{WE}$	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
µA	microampere
mA	milliampere
ns	nanosecond
Ω	ohm
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY62146ESL MoBL, 4-Mbit (256K × 16) Static RAM Document Number: 001-43142			
Rev.	**ECN No.**	**Submission Date**	**Description of Change**
**	1875228	01/02/2008	New data sheet.
*A	2944332	06/04/2010	Updated Electrical Characteristics: Added Note 8 and referred the same note in I_{SB2} parameter. Updated Truth Table: Added Note 29 and referred the same note in $\overline{CE}$ column. Updated Package Diagram: spec 51-85087 – Changed revision from *A to *C. Added Acronyms. Updated to new template.
*B	3109186	12/13/2010	Changed Table Footnotes to Footnotes. Updated Ordering Information: No change in part numbers. Added Ordering Code Definitions. Completing Sunset Review.
*C	3296704	06/29/2011	Updated Functional Description: Updated description (Removed “For best practice recommendations, refer to the Cypress Application Note AN1064, SRAM System Guidelines.”). Updated Electrical Characteristics: Updated Note 8 (Added I_{SB1}) and referred the same note in I_{SB1} parameter. Updated Capacitance: Added Note 9 and referred the same note in parameter column. Updated Thermal Resistance: Added Note 9 and referred the same note in parameter column. Updated Data Retention Characteristics: Added Note 11 and referred the same note in I_{CCDR} parameter. Changed minimum value of t_R parameter from t_{RC} to 45 ns. Updated Switching Characteristics: Moved Note 14 to parameter column. Added Units of Measure.
*D	3903350	02/13/2013	Updated Switching Waveforms: Updated Figure 6 (Removed $\overline{OE}$ signal). Updated Figure 7 (Removed $\overline{OE}$ signal). Removed the Note “Data I/O is high impedance if $\overline{OE}$ = V_{IH}.” and its reference in Figure 6, Figure 7. Removed the figure “Write Cycle 3: $\overline{WE}$ controlled, $\overline{OE}$ LOW”. Updated Figure 8 (Removed “$\overline{OE}$ LOW” in caption only). Updated Package Diagram: spec 51-85087 – Changed revision from *C to *E. Completing Sunset Review.
*E	4100920	08/21/2013	Updated Switching Characteristics: Added Note 14 and referred the same note in “Parameter” column. Updated to new template.
*F	4576406	01/16/2015	Updated Functional Description: Added “For a complete list of related documentation, click here.” at the end. Updated Switching Characteristics: Added Note 19 and referred the same note in “Write Cycle”. Updated Switching Waveforms: Added Figure 9. Added Note 28 and referred the same note in Figure 9.

Document History Page (continued)

Document Title: CY62146ESL MoBL, 4-Mbit (256K × 16) Static RAM Document Number: 001-43142			
Rev.	**ECN No.**	**Submission Date**	**Description of Change**
*G	5169392	03/10/2016	Updated Thermal Resistance: Replaced “two-layer” with “four-layer” in “Test Conditions” column. Changed value of Θ_{JA} parameter from 77 °C/W to 57.92 °C/W. Changed value of Θ_{JC} parameter from 13 °C/W to 17.44 °C/W. Updated to new template. Completing Sunset Review.
*H	5983493	12/04/2017	Updated Cypress Logo and Copyright.
*I	6529117	04/01/2019	Updated to new template. Completing Sunset Review.
*J	6906316	06/26/2020	Updated Features: Changed value of Typical standby current from 1 µA to 2.5 µA. Changed value of Typical active current from 2 mA to 3.5 mA. Updated Product Portfolio: Changed typical value of Operating I_{CC} from 2 mA to 3.5 mA corresponding to “f = 1 MHz”. Changed maximum value of Operating I_{CC} from 2.5 mA to 6 mA corresponding to “f = 1 MHz”. Changed typical value of Standby, I_{SB2} from 1 µA to 2.5 µA. Updated Electrical Characteristics: Changed typical value of I_{CC} parameter from 2 mA to 3.5 mA corresponding to Test Condition “f = 1 MHz”. Changed maximum value of I_{CC} parameter from 2.5 mA to 6 mA corresponding to Test Condition “f = 1 MHz”. Changed typical value of I_{SB1} parameter from 1 µA to 2.5 µA. Changed typical value of I_{SB2} parameter from 1 µA to 2.5 µA. Updated Data Retention Characteristics: Changed typical value of I_{CCDR} parameter from 1 µA to 3 µA. Changed maximum value of I_{CCDR} parameter from 7 µA to 8.8 µA. Updated Package Diagram: spec 51-85087 – Changed revision from *E to *F. Updated to new template.

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